

2N2151

APPLICATIONS:

- Fast Switching
- High Frequency Switching and Amplifying

FEATURES:

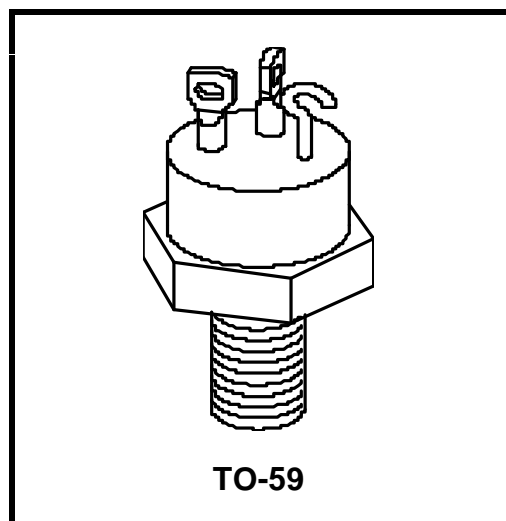
- High Reliability
- Greater Gain Stability

**5 Amp, 100V,
 Planar, NPN
 Power Transistors
 JAN, JANTX**

DESCRIPTION:

These power transistors are produced by PPC's DOUBLE DIFFUSED PLANAR process. This technology produces high voltage devices with excellent switching speeds, frequency response, gain linearity, saturation voltages, high current gain, and safe operating areas. They are intended for use in Commercial, Industrial, and Military power switching, amplifier, and regulator applications.

Ultrasonically bonded leads and controlled die mount techniques are utilized to further increase the SOA capability and inherent reliability of these devices. The temperature range to 200°C permits reliable operation in high ambients, and the hermetically sealed package insures maximum reliability and long life.



ABSOLUTE MAXIMUM RATINGS

SYMBOL	CHARACTERISTIC	VALUE	UNITS
V_{CBO}^*	Collector-Base Voltage	150	V
V_{CEO}^*	Collector-Emitter Voltage	100	V
V_{EBO}^*	Emitter-Base Voltage	8	V
I_C^*	Peak Collector Current	10	A
I_C^*	Continuous Collector Current	5	A
I_B^*	Continuous Base Current	2	A
T_{STG}^*	Storage Temperature	-65 to 200	°C
T_J^*	Operating Junction Temperature	-65 to 200	°C
*	Lead Temperature 1/16" From Case for 10 Sec.	230	°C
P_T^*	Power Dissipation $T_A = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	2 30	W W
θ_{JC}	Thermal Resistance Junction to Case	3.33	°C/W

* Indicates JEDEC registered data.

ELECTRICAL CHARACTERISTICS
(25°C Case Temperature Unless Otherwise Noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE		Units
			Min.	Max	
BV_{CBO}^*	Collector-Base Voltage	$I_C = 100 \mu\text{A}$, Cond. D	150	----	Vdc
BV_{CEO}^*	Collector-Emitter Voltage (Note 1)	$I_C = 50 \text{ mA}$, Cond. D	100	----	Vdc
BV_{EBO}^*	Emitter-Base Voltage	$I_E = 2 \mu\text{A}$, Cond. D	8	----	Vdc
I_{CEO}^*	Collector-Emitter Cutoff Current	$V_{CE} = 120 \text{ Vdc}$, Cond. D	----	5	μA
I_{CEX}^*	Collector-Emitter Cutoff Current	$V_{CE} = 120 \text{ Vdc}$, $V_{EB} = 0.5 \text{ Vdc}$, Cond. A $V_{CE} = 120 \text{ Vdc}$, $V_{EB} = 0.5 \text{ Vdc}$, Cond. A $T_A = 150^\circ\text{C}$	----	5 100	μA <u>μA</u>
I_{CBO}^*	Collector-Base Cutoff Current	$V_{CB} = 120 \text{ Vdc}$, Cond. D	----	5	μA
h_{FE}^*	DC Current Gain (Note 1)	$I_C = 1 \text{ A}$, $V_{CE} = 5 \text{ Vdc}$ $I_C = 0.5 \text{ A}$, $V_{CE} = 5 \text{ Vdc}$ $I_C = 0.1 \text{ A}$, $V_{CE} = 5 \text{ Vdc}$	40 40 40	120 120 ----	---- ---- ----
h_{FE}^*	AC Current Gain	$I_C = 0.1 \text{ A}$, $V_{CE} = 30 \text{ Vdc}$, $f = 1 \text{ KHz}$	40	160	----
$V_{CE(sat)}^*$	Collector Saturation Voltage (Note 1)	$I_C = 1 \text{ A}$, $I_B = 0.1 \text{ A}$	----	1.0	Vdc
$V_{BE(sat)}^*$	Base Saturation Voltage (Note 1)	$I_C = 1 \text{ A}$, $I_B = 0.1 \text{ A}$	----	1.2	Vdc
$V_{BE(on)}^*$	Base On-Voltage (Note 1)	$I_C = 1 \text{ A}$, $V_{CE} = 2 \text{ Vdc}$	----	1.2	Vdc
f_T^*	Gain-Bandwidth Product	$I_C = 1 \text{ A}$, $V_{CE} = 30 \text{ Vdc}$, $f = 10 \text{ MHz}$	10	70	MHz
C_{ob}^*	Output Capacitance	$V_{CB} = 20 \text{ Vdc}$, $I_E = 0$, $f = 1 \text{ MHz}$	----	160	pf

Note 1: Pulse Test: PW = 300 μs , Duty Cycle $\leq 2\%$.

* Indicates JEDEC registered data.

PACKAGE MECHANICAL DATA

